Erratum: “Effects of alloy disorder and confinement on phonon modes and Raman scattering in Si_XGe_{1-X} nanocrystals: A microscopic modeling” [J. Appl. Phys. 115, 143505 (2014)]

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Erratum: "Effects of alloy disorder and confinement on phonon modes and Raman scattering in Si_xGe_{1-x} nanocrystals: A microscopic modeling" [J. Appl. Phys. 115, 143505 (2014)]

A. S. Vasin,[1] O. V. Vikhrova,[1] and M. I. Vasilevskiy[2,a)]
[1]*Department of Physics and NIFTI, N. I. Lobachevskii University of Nizhnii Novgorod, Nizhnii Novgorod 603600, Russia*
[2]*Centro de Física, Universidade do Minho, Campus de Gualtar, 4710-057 Braga, Portugal*

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By mistake Fig. 6 of Ref. 1 contains repeated panels for the Ge-Ge vibration mode instead of those corresponding to the Si-Si and Si-Ge modes. The correct figure is presented below.

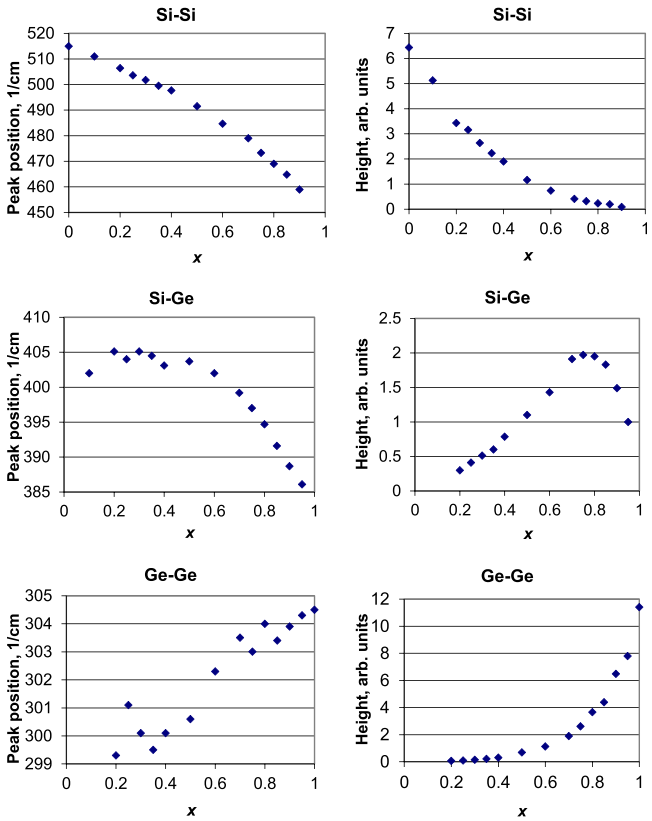

FIG. 6. Positions (left column) and heights (right column) of the main Raman peaks *versus* Ge contents for $Si_{1-x}Ge_x$ NCs calculated using Tersoff potential. NC size is 3.9 nm.

[1]A. S. Vasin, O. V. Vikhrova, and M. I. Vasilevskiy, J. Appl. Phys. **115**, 143505 (2014).

[a)]Author to whom correspondence should be addressed. Electronic mail: mikhail@fisica.uminho.pt

